

SPECIFICATION AMENDMENTS:

In the Related Application section, before paragraph [0001], please insert the following new paragraph:

This application is a division of co-pending U.S. Patent Application Serial No. 10/038,845, filed December 31, 2001, entitled "High Voltage Power MOSFET Having A Voltage Sustaining Region That Includes Doped Columns Formed By Trench Etching And Ion Implantation."